

## MF-1K-PW MIFARE 1K Adhesive Wafer

#### Product data sheet COMPANY PUBLIC

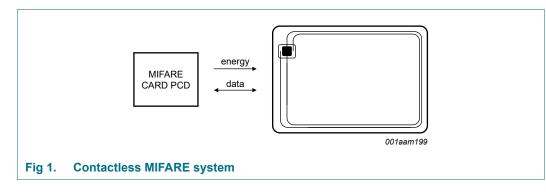
## 1. General description

NXP Semiconductors has developed the MIFARE Classic MF1S50yyX/V1 to be used in a contactless smart card according to ISO/IEC 14443 Type A.

The MIFARE Classic EV1 1K MF1S50yyX/V1 IC is used in applications like public transport ticketing and can also be used for various other applications.

### 1.1 Anticollision

An intelligent anticollision function allows to operate more than one card in the field simultaneously. The anticollision algorithm selects each card individually and ensures that the execution of a transaction with a selected card is performed correctly without interference from another card in the field.



#### 1.2 Simple integration and user convenience

The MF1S50yyX/V1 is designed for simple integration and user convenience which allows complete ticketing transactions to be handled in less than 100 ms.

### 1.3 Security and privacy

- Manufacturer programmed 7-byte UID or 4-byte NUID identifier for each device
- Random ID support
- Mutual three pass authentication (ISO/IEC DIS 9798-2)
- Individual set of two keys per sector to support multi-application with key hierarchy



#### MIFARE Classic EV1 1K - Mainstream contactless smart card IC

#### 1.4 Delivery options

- 7-byte UID, 4-byte NUID
- Bumped die on sawn wafer
- MOA4 and MOA8 contactless module

#### Features and benefits 2.

- Contactless transmission of data and energy supply
- Operating frequency of 13.56 MHz
- Data integrity of 16-bit CRC, parity, bit coding, bit counting
- Typical ticketing transaction time of < 100 ms (including backup management)
- Random ID support (7 Byte UID version) NXP Originality Check support

#### 2.1 EEPROM

- 1 kB, organized in 16 sectors of 4 blocks User definable access conditions for (one block consists of 16 byte)
- Data retention time of 10 years

- Operating distance up to 100 mm depending on antenna geometry and reader configuration
- Data transfer of 106 kbit/s
- Anticollision

7 Byte UID or 4 Byte NUID

- each memory block
- Write endurance 200000 cycles

#### **Applications** 3.

- Public transportation
- Electronic toll collection
- School and campus cards
- Internet cafés

- Access management
- Car parking
- Employee cards
  - Loyalty

#### Quick reference data 4.

Table 1. Quick reference	Table 1.	Quick reference
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data		Conditions		Min	Тур	Max	Unit
Symbol	Phpratrocepencitance		[1]	14.9	16.9	19.0	pF
f <sub>i</sub>	input frequency			-	13.56	-	MHz
EEPROM	characteristics						
t <sub>ret</sub>	retention time	T <sub>amb</sub> = 22 °C		10	-	-	year
N <sub>endu(W)</sub>	write endurance	T <sub>amb</sub> = 22 °C		100000	200000	-	cycle

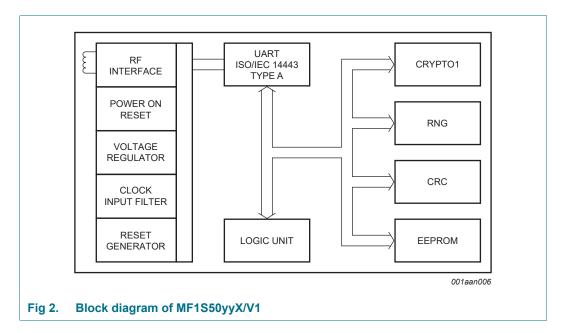
[1] T<sub>amb</sub>=22°C, f=13,56Mhz, V<sub>LaLb</sub> = 1,5 V RMS

MF1S50yyX\_V1

## 5. Ordering information

Table 2.	Ordering		
information			
Type number	Package	Description	Version
MF1S5001XDUD/V1	F <b>Nanbe</b> ump	8 inch wafer, 120 $\mu m$ thickness, on film frame carrier, electronic fail die marking according to SECS-II format), Au bumps, 7-byte UID	-
MF1S5001XDUF/V1	FFC Bump	8 inch wafer, 75 $\mu m$ thickness, on film frame carrier, electronic fail die marking according to SECS-II format), Au bumps, 7-byte UID	-
MF1S5000XDA4/V1	MOA4	plastic leadless module carrier package; 35 mm wide tape, 7-byte UID	SOT500-2
MF1S5000XDA8/V1	MOA8	plastic leadless module carrier package; 35 mm wide tape, 7-byte UID	SOT500-4
MF1S5031XDUD/V1	FFC Bump	8 inch wafer, 120 $\mu$ m thickness, on film frame carrier, electronic fail die marking according to SECS-II format), Au bumps, 4-byte non-unique ID	-
MF1S5031XDUF/V1	FFC Bump	8 inch wafer, 75 $\mu$ m thickness, on film frame carrier, electronic fail die marking according to SECS-II format), Au bumps, 4-byte non-unique ID	-
MF1S5030XDA4/V1	MOA4	plastic leadless module carrier package; 35 mm wide tape, 4-byte non-unique ID	SOT500-2
MF1S5030XDA8/V1	MOA8	plastic leadless module carrier package; 35 mm wide tape, 4-byte non-unique ID	SOT500-4

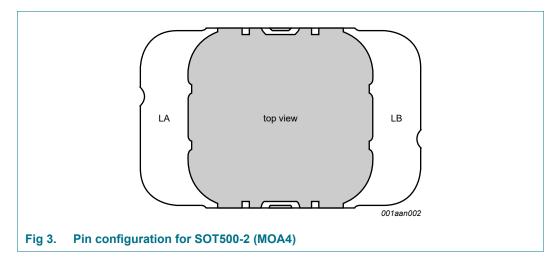
### 6. Block diagram



## 7. Pinning information

#### 7.1 Pinning

The pinning for the MF1S50yyX/V1DAx is shown as an example in <u>Figure 3</u> for the MOA4 contactless module. For the contactless module MOA8, the pinning is analogous and not explicitly shown.



#### Table 3.Pin allocation table

Pin	Symbol	
LA	LA	Antenna coil connection LA
LB	LB	Antenna coil connection LB

### 8. Functional description

#### 8.1 Block description

The MF1S50yyX/V1 chip consists of a 1 kB EEPROM, RF interface and Digital Control Unit. Energy and data are transferred via an antenna consisting of a coil with a small number of turns which is directly connected to the MF1S50yyX/V1. No further external components are necessary. Refer to the document Ref. 1 for details on antenna design.

- RF interface:
  - Modulator/demodulator
  - Rectifier
  - Clock regenerator
  - Power-On Reset (POR)
  - Voltage regulator
- Anticollision: Multiple cards in the field may be selected and managed in sequence
- Authentication: Preceding any memory operation the authentication procedure ensures that access to a block is only possible via the two keys specified for each block
- Control and Arithmetic Logic Unit: Values are stored in a special redundant format and can be incremented and decremented
- EEPROM interface
- Crypto unit: The CRYPTO1 stream cipher of the MF1S50yyX/V1 is used for authentication and encryption of data exchange.
- EEPROM: 1 kB is organized in 16 sectors of 4 blocks. One block contains 16 bytes. The last block of each sector is called "trailer", which contains two secret keys and programmable access conditions for each block in this sector.

### 8.2 Communication principle

The commands are initiated by the reader and controlled by the Digital Control Unit of the MF1S50yyX/V1. The command response is depending on the state of the IC and for memory operations also on the access conditions valid for the corresponding sector.

#### 8.2.1 Request standard / all

After Power-On Reset (POR) the card answers to a request REQA or wakeup WUPA command with the answer to request code (see <u>Section 9.4</u>, ATQA according to ISO/IEC 14443A).

#### 8.2.2 Anticollision loop

In the anticollision loop the identifier of a card is read. If there are several cards in the operating field of the reader, they can be distinguished by their identifier and one can be selected (select card) for further transactions. The unselected cards return to the idle state and wait for a new request command. If the 7-byte UID is used for anticollision and selection, two cascade levels need to be processes as defined in ISO/IEC 14443-3.

**Remark:** For the 4-byte non-unique ID product versions, the identifier retrieved from the card is not defined to be unique. For further information regarding handling of non-unique identifiers see <u>Ref. 6</u>.

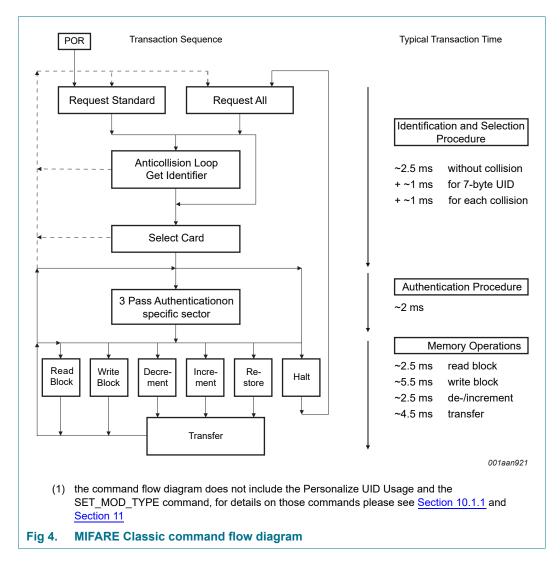
#### 8.2.3 Select card

With the select card command the reader selects one individual card for authentication and memory related operations. The card returns the Select AcKnowledge (SAK) code which determines the type of the selected card, see Section 9.4. For further details refer to the document Ref. 2.

#### 8.2.4 Three pass authentication

After selection of a card the reader specifies the memory location of the following memory access and uses the corresponding key for the three pass authentication procedure. After a successful authentication all commands and responses are encrypted.

**Remark:** The HLTA command needs to be sent encrypted to the PICC after a successful authentication in order to be accepted.



MF1S50yyX\_V1

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#### 8.2.5 Memory operations

After authentication any of the following operations may be performed:

- Read block
- Write block
- Decrement: Decrements the contents of a block and stores the result in the internal Transfer Buffer
- Increment: Increments the contents of a block and stores the result in the internal Transfer Buffer
- Restore: Moves the contents of a block into the internal Transfer Buffer
- Transfer: Writes the contents of the internal Transfer Buffer to a value block

#### 8.3 Data integrity

Following mechanisms are implemented in the contactless communication link between reader and card to ensure very reliable data transmission:

- 16 bits CRC per block
- · Parity bits for each byte
- Bit count checking
- Bit coding to distinguish between "1", "0" and "no information"
- Channel monitoring (protocol sequence and bit stream analysis)

#### 8.4 Three pass authentication sequence

- 1. The reader specifies the sector to be accessed and chooses key A or B.
- 2. The card reads the secret key and the access conditions from the sector trailer. Then the card sends a number as the challenge to the reader (pass one).
- 3. The reader calculates the response using the secret key and additional input. The response, together with a random challenge from the reader, is then transmitted to the card (pass two).
- 4. The card verifies the response of the reader by comparing it with its own challenge and then it calculates the response to the challenge and transmits it (pass three).
- 5. The reader verifies the response of the card by comparing it to its own challenge.

After transmission of the first random challenge the communication between card and reader is encrypted.

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#### 8.5 RF interface

The RF-interface is according to the standard for contactless smart cards ISO/IEC 14443A.

For operation, the carrier field from the reader always needs to be present (with short pauses when transmitting), as it is used for the power supply of the card.

For both directions of data communication there is only one start bit at the beginning of each frame. Each byte is transmitted with a parity bit (odd parity) at the end. The LSB of the byte with the lowest address of the selected block is transmitted first. The maximum frame length is 163 bits (16 data bytes + 2 CRC bytes =  $16 \times 9 + 2 \times 9 + 1$  start bit).

#### 8.6 Memory organization

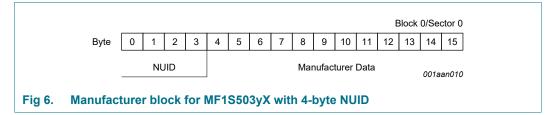
The  $1024 \times 8$  bit EEPROM memory is organized in 16 sectors of 4 blocks. One block contains 16 bytes.

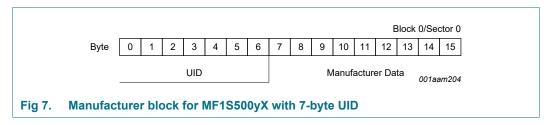
<u> </u>	<b>D</b> 1 1	ıŀ				_		· ·			with				40	40		45		
Sector	Block		0	1	2	3	4	5	6	7	8	9	10	11			14	15		scription
15	3				Ke	yА			A		ss Bi	ts			Ke	у В			Sec	tor Trailer 15
	2																		Dat	а
	1																		Dat	а
	0																		Dat	а
14	3				Ke	yА			A	cces	ss Bi	ts			Ke	yВ			Sec	tor Trailer 14
	2																		Dat	а
	1																		Dat	а
	0																		Dat	а
		1																		
:	:																			
:	:																			
:	:																			
1	3				Ke	yА			A	cces	ss Bi	ts			Ke	yВ			Sec	tor Trailer 1
	2																		Dat	а
	1																		Dat	а
	0																		Dat	а
0	3	1			Ke	yА			A	cces	ss Bi	ts			Ke	yВ			Sec	tor Trailer 0
	2																		Dat	а
	1																		Dat	а
	0					1	1	N	/anu	ufact	urer	Dat	а						Mai	nufacturer Block
																				001aan0

Fig 5. Memory organiza

#### 8.6.1 Manufacturer block

This is the first data block (block 0) of the first sector (sector 0). It contains the IC manufacturer data. This block is programmed and write protected in the production test. The manufacturer block is shown in <u>Figure 6</u> and <u>Figure 7</u> for the 4-byte NUID and 7-byte UID version respectively.





#### 8.6.2 Data blocks

All sectors contain 3 blocks of 16 bytes for storing data (Sector 0 contains only two data blocks and the read-only manufacturer block).

The data blocks can be configured by the access bits as

- read/write blocks
- value blocks

Value blocks can be used for e.g. electronic purse applications, where additional commands like increment and decrement for direct control of the stored value are provided

A successful authentication has to be performed to allow any memory operation.

Remark: The default content of the data blocks at delivery is not defined.

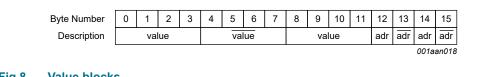
#### 8.6.2.1 Value blocks

Value blocks allow performing electronic purse functions (valid commands are: read, write, increment, decrement, restore, transfer). Value blocks have a fixed data format which permits error detection and correction and a backup management.

A value block can only be generated through a write operation in value block format:

• Value: Signifies a signed 4-byte value. The lowest significant byte of a value is stored in the lowest address byte. Negative values are stored in standard 2's complement format. For reasons of data integrity and security, a value is stored three times, twice non-inverted and once inverted.

• Adr: Signifies a 1-byte address, which can be used to save the storage address of a block, when implementing a powerful backup management. The address byte is stored four times, twice inverted and non-inverted. During increment, decrement, restore and transfer operations the address remains unchanged. It can only be altered via a write command.



#### Fig 8. Value blocks

An example of a valid value block format for the decimal value 1234567d and the block address 17d is shown in <u>Table 4</u>. First, the decimal value has to be converted to the hexadecimal representation of 0012D687h. The LSByte of the hexadecimal value is stored in Byte 0, the MSByte in Byte 3. The bit inverted hexadecimal representation of the value is FFED2978h where the LSByte is stored in Byte 4 and the MSByte in Byte 7.

The hexadecimal value of the address in the example is 11h, the bit inverted hexadecimal value is EEh.

#### Table 4.Value block format example

Byte Number	0	1	2	3	4	5	6	7	8	9	10	11	12	1:	3	14	15
Description	valu	e			valu	e			valu	е			а	ıdr a	dr a	adr a	dr
Values [hex]	87	D6	12	00	78	29	ED	FF	87	D6	12	00	11	EE	11	EE	

#### 8.6.3 Sector trailer

The sector trailer is the last block (block 3) in one sector. Each sector has a sector trailer containing the

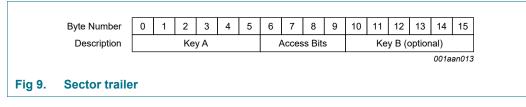
- secret keys A (mandatory) and B (optional), which return logical "0"s when read and
- the access conditions for the blocks of that sector, which are stored in bytes 6...9. The access bits also specify the type (data or value) of the data blocks.

If key B is not needed, the last 6 bytes of the sector trailer can be used as data bytes. The access bits for the sector trailer have to be configured accordingly, see <u>Section 8.7.2</u>.

Byte 9 of the sector trailer is available for user data. For this byte the same access rights as for byte 6, 7 and 8 apply.

When the sector trailer is read, the key bytes are blanked out by returning logical zeros. If key B is configured to be readable, the data stored in bytes 10 to 15 is returned, see <u>Section 8.7.2</u>.

All keys are set to FFFF FFFF FFFFh at chip delivery and the bytes 6, 7 and 8 are set to FF0780h.



#### 8.7 Memory access

Before any memory operation can be done, the card has to be selected and authenticated as described in <u>Section 8.2</u>. The possible memory operations for an addressed block depend on the key used during authentication and the access conditions stored in the associated sector trailer.

Table 5.	Memory	
operations		Valid for Block Type
<b>Oper</b> dation	Dessisription emory block	read/write, value and sector trailer
Write	writes one memory block	read/write, value and sector trailer
Increment	increments the contents of a block and stores the result in the internal Transfer Buffer	value
Decrement	decrements the contents of a block and stores the result in the internal Transfer Buffer	value
Transfer	writes the contents of the internal Transfer Buffer to a block	value and read/write
Restore	reads the contents of a block into the internal Transfer Buffer	value

#### 8.7.1 Access conditions

The access conditions for every data block and sector trailer are defined by 3 bits, which are stored non-inverted and inverted in the sector trailer of the specified sector.

The access bits control the rights of memory access using the secret keys A and B. The access conditions may be altered, provided one knows the relevant key and the current access condition allows this operation.

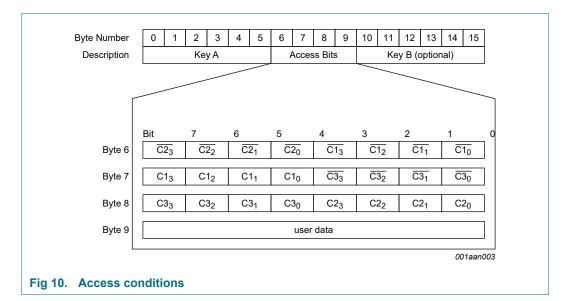
**Remark:** With each memory access the internal logic verifies the format of the access conditions. If it detects a format violation the whole sector is irreversibly blocked.

**Remark:** In the following description the access bits are mentioned in the non-inverted mode only.

The internal logic of the MF1S50yyX/V1 ensures that the commands are executed only after a successful authentication.

Access Bits	Valid Commands		Block	Description
C1 <sub>3</sub> , C2 <sub>3</sub> , C3 <sub>3</sub>	read, write	$\rightarrow$	3	sector trailer
C1 <sub>2</sub> , C2 <sub>2</sub> , C3 <sub>2</sub>	read, write, increment, decrement, transfer, restore	$\rightarrow$	2	data block
C1 <sub>1</sub> , C2 <sub>1</sub> , C3 <sub>1</sub>	read, write, increment, decrement, transfer, restore	$\rightarrow$	1	data block
C1 <sub>0</sub> ,C2 <sub>0</sub> , C3 <sub>0</sub>	read, write, increment, decrement, transfer, restore	$\rightarrow$	0	data block

#### Table 6. Access conditions



#### 8.7.2 Access conditions for the sector trailer

Depending on the access bits for the sector trailer (block 3) the read/write access to the keys and the access bits is specified as 'never', 'key A', 'key B' or key A|B' (key A or key B).

On chip delivery the access conditions for the sector trailers and key A are predefined as transport configuration. Since key B may be read in the transport configuration, new cards must be authenticated with key A. Since the access bits themselves can also be blocked, special care has to be taken during the personalization of cards.

Acc	ess b	oits	Access of	condition	for	Remark			
			KEYA		Access	bits	KEYB		
C1	C2	C3	read wr	ite read		write r	ead	write	
0	0	0	never	key A	key A	never	key A	key A	Key B may be read <sup>[1]</sup>
0	1	0	never	never	key A	never	key A	never	Key B may be read <sup>[1]</sup>
1	0	0	never	key B	key	A B	never i	never	key B
1	1	0	never	never	key A	B ne	ver nev	er ne	ever
0	0	1	never	key A	key A	key A	key A	key A	Key B may be read, transport configuration <sup>[1]</sup>
0	1	1	never	key B	key	A B	key B	neve	r key B
1	0	1	never	never	key A	B key	/ В	never	never
1	1	1	never	never	key A	B nev	ver nev	er ne	ever

#### Table 7. Access conditions for the sector trailer

[1] For this access condition key B is readable and may be used for data

#### MIFARE Classic EV1 1K - Mainstream contactless smart card IC

#### 8.7.3 Access conditions for data blocks

Depending on the access bits for data blocks (blocks 0...2) the read/write access is specified as 'never', 'key A', 'key B' or 'key A|B' (key A or key B). The setting of the relevant access bits defines the application and the corresponding applicable commands.

- Read/write block: the operations read and write are allowed.
- Value block: Allows the additional value operations increment, decrement, transfer and restore. With access condition '001' only read and decrement are possible which reflects a non-rechargeable card. For access condition '110' recharging is possible by using key B.
- Manufacturer block: the read-only condition is not affected by the access bits setting!
- Key management: in transport configuration key A must be used for authentication

Acc	ess bit	ts	Acces	s condi	tion for						Applica	tion	
C1	C2	C3	read		write		increm	ient	decre	ement, tra	nsfer, res	tore	
0	0		0	key	A	В	key	Ale	3	key	A B	key	AJB
											configura	ation <sup>[1]</sup>	
0	1	0	key	A B	never		neve	r	neve	r	read/wri	te block <sup>[1]</sup>	
1	_	0	0		key		AB	key	-	В	nev	er _	never
1	1	0	key	A B	key	В	key	В	key	A B	value	block <sup>[1]</sup>	
0	0	1	key	A B	never		never	key	A	B	value	block <sup>[1]</sup>	
0	1		1	key		В	ke	у	В	n	ever	never	rea
1	0		1	key		В	ne	ver	n	ever	neve	er _	read/write
1	1	1	never	nev	er		never	neve	∋r		read/wri	te bloc	k

#### Table 8. Access conditions for data blocks

[1] If key B may be read in the corresponding Sector Trailer it cannot serve for authentication (see grey marked lines in <u>Table 7</u>). As a consequences, if the reader authenticates any block of a sector which uses such access conditions for the Sector Trailer and using key B, the card will refuse any subsequent memory access after authentication.

MF1S50yyX\_V1

#### MIFARE Classic EV1 1K - Mainstream contactless smart card IC

### 9. Command overview

The MIFARE Classic card activation follows the ISO/IEC 14443 Type A. After the MIFARE Classic card has been selected, it can either be deactivated using the ISO/IEC 14443 Halt command, or the MIFARE Classic commands can be performed. For more details about the card activation refer to <u>Ref. 4</u>.

#### 9.1 MIFARE Classic command overview

All MIFARE Classic commands typically use the MIFARE CRYPTO1 and require an authentication.

All available commands for the MIFARE Classic EV1 1K are shown in Table 9.

Command	ISO/IEC 14443	Command code (hexadecimal)
Request	REQA	26h (7 bit)
Wake-up	WUPA	52h (7 bit)
Anticollision CL1	Anticollision CL1	93h 20h
Select CL1	Select CL1	93h 70h
Anticollision CL2	Anticollision CL2	95h 20h
Select CL2	Select CL2	95h 70h
Halt	Halt	50h 00h
Authentication with Key A	-	60h
Authentication with Key B	-	61h
Personalize UID Usage	-	40h
SET_MOD_TYPE	-	43h
MIFARE Read	-	30h
MIFARE Write	-	A0h
MIFARE Decrement	-	C0h
MIFARE Increment	-	C1h
MIFARE Restore	-	C2h
MIFARE Transfer	-	B0h

#### Table 9.Command overview

All commands use the coding and framing as described in <u>Ref. 3</u> and <u>Ref. 4</u> if not otherwise specified.

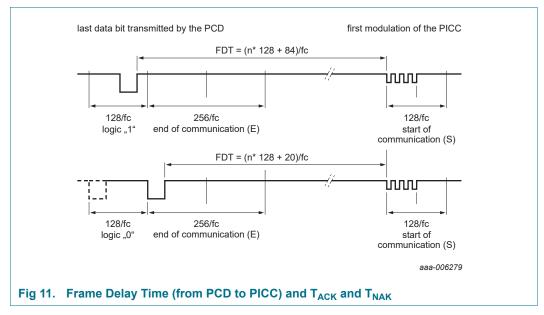
#### 9.2 Timings

The timing shown in this document are not to scale and values are rounded to 1  $\mu$ s.

All given times refer to the data frames including start of communication and end of communication. A PCD data frame contains the start of communication (1 "start bit") and the end of communication (one logic 0 + 1 bit length of unmodulated carrier). A PICC data frame contains the start of communication (1 "start bit") and the end of communication (1 bit length of no subcarrier).

The minimum command response time is specified according to Ref. 4 as an integer **n** which specifies the PCD to PICC frame delay time. The frame delay time from PICC to PCD is at least 87  $\mu$ s. The maximum command response time is specified as a time-out value. Depending on the command, the T<sub>ACK</sub> value specified for command responses defines the PCD to PICC frame delay time. It does it for either the 4-bit ACK value specified in Section 9.3 or for a data frame.

All command timings are according to ISO/IEC 14443-3 frame specification as shown for the Frame Delay Time in Figure 11. For more details refer to Ref. 3 and Ref. 4.



**Remark:** Due to the coding of commands, the measured timings usually excludes (a part of) the end of communication. Consider this factor when comparing the specified with the measured times.

#### 9.3 MIFARE Classic ACK and NAK

The MIFARE Classic uses a 4 bit ACK / NAK as shown in Table 10.

#### Table 10. MIFARE ACK and NAK

Code (4-bit)	Transfer Buffer Validity	Description
Ah		Acknowledge (ACK)
0h	valid	invalid operation
1h	valid	parity or CRC error
4h	invalid	invalid operation
5h	invalid	parity or CRC error

#### 9.4 ATQA and SAK responses

For details on the type identification procedure please refer to Ref. 2.

The MF1S50yyX/V1 answers to a REQA or WUPA command with the ATQA value shown in <u>Table 11</u> and to a Select CL1 command (CL2 for the 7-byte UID variant) with the SAK value shown in <u>Table 12</u>.

#### Table 11. ATQA response of the MF1S50yyX/V1

		Bit Number															
Sales Type	Hex Value	16 1	51	4 1	31	2 1	1 10	9	8	7	65	4	32				
MF1S500yX	00 44h	0	0	0	0	0	0	C		0	0	1	0	0	0	1	0
MF1S503yX	00 04h	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0

#### Table 12. SAK response of the MF1S50yyX/V1

		Bit Number						
Sales Type	Hex Value	8 7	6	5	4	3	2	1
MF1S50yyX/V1	08h	0 0	0	0	1	0	0	0

**Remark:** The ATQA coding in bits 7 and 8 indicate the UID size according to ISO/IEC 14443 independent from the settings of the UID usage.

**Remark:** The bit numbering in the ISO/IEC 14443 starts with LSBit = bit 1, but not LSBit = bit 0. So one byte counts bit 1 to 8 instead of bit 0 to 7.

MF1S50yyX\_V1

1 0

### **10. UID Options and Handling**

The MF1S50yyX/V1 product family offers two delivery options for the UID which is stored in block 0 of sector 0.

- 7-byte UID
- 4-byte NUID (Non-Unique ID)

This section describes the MIFARE Classic MF1S50yyX/V1 operation when using one of the 2 UID options with respect to card selection, authentication and personalization. See also <u>Ref. 6</u> for details on how to handle UIDs and NUIDs with MIFARE Classic products.

#### 10.1 7-byte UID Operation

All MF1S50**0**yXDyy products are featuring a 7-byte UID. This 7-byte UID is stored in block 0 of sector 0 as shown in <u>Figure 7</u>. The behaviour during anti-collision, selection and authentication can be configured during personalization for this UID variant.

#### **10.1.1 Personalization Options**

The 7-byte UID variants of the MF1S50yyX/V1 can be operated with four different functionalities, denoted as UIDFn (UID Functionality n).

- 1. UIDF0: anti-collision and selection with the double size UID according to ISO/IEC 14443-3
- 2. UIDF1: anti-collision and selection with the double size UID according to ISO/IEC 14443-3 and optional usage of a selection process shortcut
- 3. UIDF2: anti-collision and selection with a single size random ID according to ISO/IEC 14443-3
- 4. UIDF3: anti-collision and selection with a single size NUID according to ISO/IEC 14443-3 where the NUID is calculated out of the 7-byte UID

The anti-collision and selection procedure and the implications on the authentication process are detailed in <u>Section 10.1.2</u> and <u>Section 10.1.3</u>.

The default configuration at delivery is option 1 which enables the ISO/IEC 14443-3 compliant anti-collision and selection. This configuration can be changed using the 'Personalize UID Usage' command. The execution of this command requires an authentication to sector 0. Once this command has been issued and accepted by the PICC, the configuration is automatically locked. A subsequently issued 'Personalize UID Usage' command is not executed and a NAK is replied by the PICC.

**Remark:** As the configuration is changeable at delivery, it is strongly recommended to send this command at personalization of the card to prevent unwanted changes in the field. This should also be done if the default configuration is used.

**Remark:** The configuration becomes effective only after PICC unselect or PICC field reset.

#### MIFARE Classic EV1 1K - Mainstream contactless smart card IC

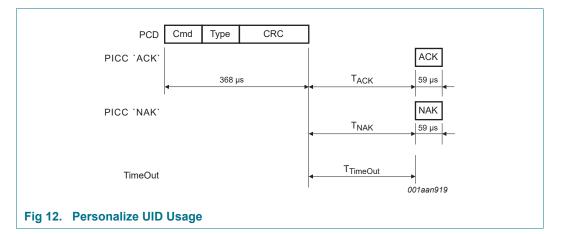


Table 13. Personalize UID Usage command

Name	Code	Description	Length
Cmd	40h	Set anti-collision, selection and authentication behaviour	1 byte
Туре	-	Encoded type of UID usage:	1 byte
		UIDF0:00h	
		UIDF1:40h	
		UIDF2:20h	
		UIDF3:60h	
CRC	-	CRC according to Ref. 4	2 bytes
ACK, NAK	see Table 10	see Section 9.3	4-bit

#### Table 14. Personalize UID Usage timing

	T <sub>ACK</sub> min	T <sub>ACK</sub> max	T <sub>NAK min</sub>	T <sub>NAK max</sub>	T <sub>TimeOut</sub>
Personalize UID Usage	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	10 ms

#### 10.1.2 Anti-collision and Selection

Depending on the chosen personalization option there are certain possibilities to perform anti-collision and selection. To bring the MIFARE Classic into the ACTIVE state according to ISO/IEC 14443-3, the following sequences are available.

Sequence 1: ISO/IEC 14443-3 compliant anti-collision and selection using the cascade level 1 followed by the cascade level 2 SEL command

Sequence 2: using cascade level 1 anti-collision and selection procedure followed by a Read command from block 0

Sequence 3: ISO/IEC 14443-3 compliant anti-collision and selection using the cascade level 1 SEL command

**Remark:** The Read from Block 0 in Sequence 2 does not require a prior authentication to Sector 0 and is transmitted in plain data. For all other sequences, the readout from Block 0 in Sector 0 is encrypted and requires an authentication to that sector.

Remark: The settings done with Personalize UID Usage do not change the ATQA coding.

Table To. Available delivation sequences for r-byte of b options							
UID Functionality	Available Activation Sequences						
UIDF0	Sequence 1						
UIDF1	Sequence 1, Sequence 2						
UIDF2	Sequence 3						
UIDF3	Sequence 3						

 Table 15.
 Available activation sequences for 7-byte UID options

#### **10.1.3** Authentication

During the authentication process, 4-byte of the UID are passed on to the MIFARE Classic Authenticate command of the contactless reader IC. Depending on the activation sequence, those 4-byte are chosen differently. In general, the input parameter to the MIFARE Classic Authenticate command is the set of 4 bytes retrieved during the last cascade level from the ISO/IEC 14443-3 Type A anticollision.

Table 16.	Input parameter to MIFARE Classic Authenticate

UID Functionality Input to MIFARE Classic Authenticate Command					
Sequence 1	CL2 bytes (UID3UID6)				
Sequence 2	CL1 bytes (CT, UID0UID2)				
Sequence 3	4-byte NUID/RID (UID0UID3)				

#### 10.2 4-byte UID Operation

All MF1S50**3**yXDyy products are featuring a 4-byte NUID. This 4-byte NUID is stored in block 0 of sector 0 as shown in Figure 6.

#### 10.2.1 Anti-collision and Selection

The anti-collision and selection process for the product variants featuring 4-byte NUIDs is done according to ISO/IEC 14443-3 Type A using cascade level 1 only.

#### 10.2.2 Authentication

The input parameter to the MIFARE Classic Authenticate command is the full 4-byte UID retrieved during the anti-collision procedure. This is the same as for the activation Sequence 3 in the 7-byte UID variant.

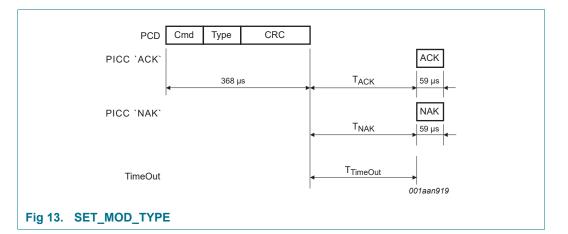
### **11. Load Modulation Strength Option**

The MIFARE Classic EV1 1K features the possibility to set the load modulation strength to high or normal. The default level is set to a high modulation strength and it is recommended for optimal performance to maintain this level and only switch to the low load modulation strength if the contactless system requires it.

**Remark:** The configuration becomes effective only after a PICC unselect or a PICC field reset. The configuration can be changed multiple times by asserting the command.

**Remark:** The MIFARE Classic EV1 1K needs to be authenticated to sector 0 with Key A to perform the SET\_MOD\_TYPE command. The Access Bits for sector 0 are irrelevant.

#### MIFARE Classic EV1 1K - Mainstream contactless smart card IC



#### Table 17. SET\_MOD\_TYPE command

Name	Code	Description	Length
Cmd	43h	Set load modulation strength	1 byte
Туре	-	Encoded load modulation strength:	1 byte
		strong modulation:01h (default)	
		normal modulation:00h	
CRC	-	CRC according to Ref. 4	2 bytes
ACK, NAK	see Table 10	see Section 9.3	4-bit

#### Table 18. SET\_MOD\_TYPE timing

	T <sub>ACK</sub> min	T <sub>ACK</sub> max	T <sub>NAK min</sub>	T <sub>NAK max</sub>	T <sub>TimeOut</sub>
SET_MOD_TYPE	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	5 ms

The configured load modulation is shown in the manufacturer data of block 0 in sector 0. The exact location is shown below in Figure 14 and Table 19.

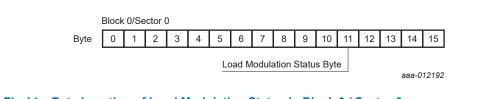


Fig 14. Byte Location of Load Modulation Status in Block 0 / Sector 0

#### Table 19. Load Modulation Status Indication

					Bit N	lumb	ər						
Load Modulation Type			Hex	Value		7	6	5	4	3	2	1	
strong	load	modulat	ion	20h	(default)	0	0	1		D	0	0	0
normal	load	modula	tion	00h		0	0	0	0	0	0	0	0

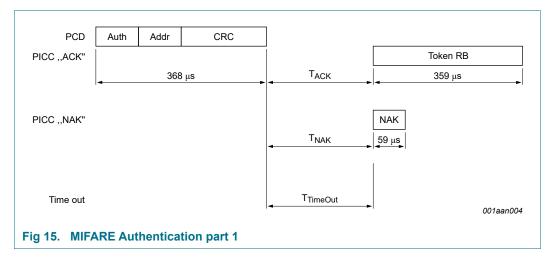
**0** 0

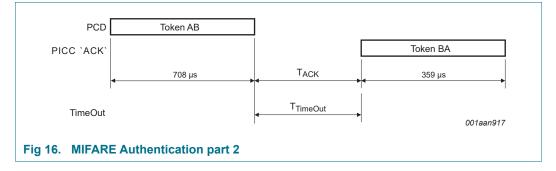
### **12. MIFARE Classic commands**

#### 12.1 MIFARE Authentication

The MIFARE authentication is a 3-pass mutual authentication which needs two pairs of command-response. These two parts, MIFARE authentication part 1 and part 2 are shown in Figure 15, Figure 16 and Table 20.

Table 21 shows the required timing.





#### Table 20. MIFARE authentication command

Name	Code	Description	Length
Auth (with Key A)	60h	Authentication with Key A	1 byte
Auth (with Key B)	61h	Authentication with Key B	1 byte
Addr	-	MIFARE Block address (00h to FFh)	1 byte
CRC	-	CRC according to <u>Ref. 4</u>	2 bytes
Token RB	-	Challenge 1 (Random Number)	4 bytes
Token AB	-	Challenge 2 (encrypted data)	8 bytes
Token BA	-	Challenge 2 (encrypted data)	4 bytes
NAK	see <u>Table 10</u>	see Section 9.3	4-bit

MF1S50yyX\_V1 Product data sheet COMPANY PUBLIC

#### Table 21. MIFARE authentication timing

	T <sub>ACK</sub> min	T <sub>ACK</sub> max	T <sub>NAK min</sub>	T <sub>NAK max</sub>	T <sub>TimeOut</sub>
Authentication part 1	n=9	T <sub>TimeOut</sub>	n=9	n=9	1 ms
Authentication part 2	n=9	T <sub>TimeOut</sub>			1 ms

**Remark:** The minimum required time between MIFARE Authentication part 1 and part 2 is the minimum required FDT according to <u>Ref. 4</u>. There is no maximum time specified.

**Remark:** The MIFARE authentication and encryption requires an MIFARE reader IC (e.g. the CL RC632). For more details about the authentication command refer to the corresponding data sheet (e.g. <u>Ref. 5</u>). The 4-byte input parameter for the MIFARE Classic Authentication is detailed in <u>Section 10.1.3</u> and <u>Section 10.2.2</u>.

#### 12.2 MIFARE Read

The MIFARE Read requires a block address, and returns the 16 bytes of one MIFARE Classic block. The command structure is shown in Figure 17 and Table 22.

Table 23 shows the required timing.

PCD	Cmd	Addr	CRC			
PICC ,,ACK"					Data	CRC
	•	368	μs	TACK	- 154	8 μs
PICC ,,NAK"					NAK	
				T <sub>NAK</sub>	59 μs	
					1	
Time out				T <sub>TimeOut</sub>	-	001aan014
Fig 17. MIFARE Read						

#### Table 22. MIFARE Read command

Name	Code	Description	Length
Cmd	30h	Read one block	1 byte
Addr	-	MIFARE Block address (00h to FFh)	1 byte
CRC	-	CRC according to <u>Ref. 4</u>	2 bytes
Data	-	Data content of the addressed block	16 bytes
NAK	see Table 10	see Section 9.3	4-bit

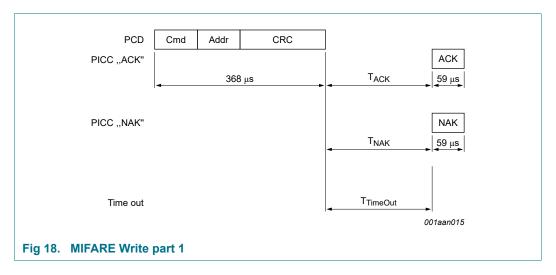
#### Table 23. MIFARE Read timing

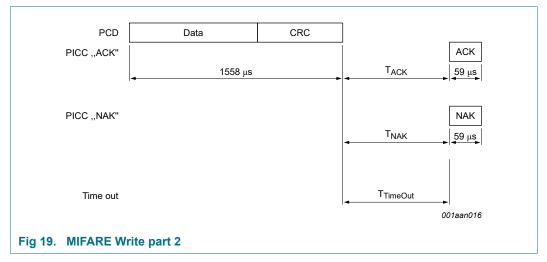
	T <sub>ACK</sub> min	T <sub>ACK</sub> max	T <sub>NAK min</sub>	T <sub>NAK max</sub>	T <sub>TimeOut</sub>
Read	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	5 ms

#### 12.3 MIFARE Write

The MIFARE Write requires a block address, and writes 16 bytes of data into the addressed MIFARE Classic EV1 1K block. It needs two pairs of command-response. These two parts, MIFARE Write part 1 and part 2 are shown in Figure 18 and Figure 19 and Table 24.

Table 25 shows the required timing.





#### Table 24. MIFARE Write command

Name	Code	Description	Length
Cmd	A0h	Write one block	1 byte
Addr	-	MIFARE Block or Page address (00h to FFh)	1 byte
CRC	-	CRC according to <u>Ref. 4</u>	2 bytes
Data	-	Data	16 bytes
NAK	see <u>Table 10</u>	see <u>Section 9.3</u>	4-bit

MF1S50yyX\_V1 Product data sheet COMPANY PUBLIC

#### Table 25. MIFARE Write timing

	T <sub>ACK</sub> min	T <sub>ACK</sub> max	T <sub>NAK min</sub>	T <sub>NAK max</sub>	T <sub>TimeOut</sub>
Write part 1	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	5 ms
Write part 2	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	10 ms

**Remark:** The minimum required time between MIFARE Write part 1 and part 2 is the minimum required FDT according to <u>Ref. 4</u>. There is no maximum time specified.

#### 12.4 MIFARE Increment, Decrement and Restore

The MIFARE Increment requires a source block address and an operand. It adds the operand to the value of the addressed block, and stores the result in the Transfer Buffer.

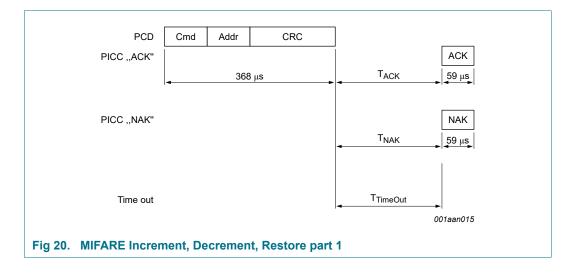
The MIFARE Decrement requires a source block address and an operand. It subtracts the operand from the value of the addressed block, and stores the result in the Transfer Buffer.

The MIFARE Restore requires a source block address. It copies the value of the addressed block into the Transfer Buffer. The 4 byte Operand in the second part of the command is not used and may contain arbitrary values.

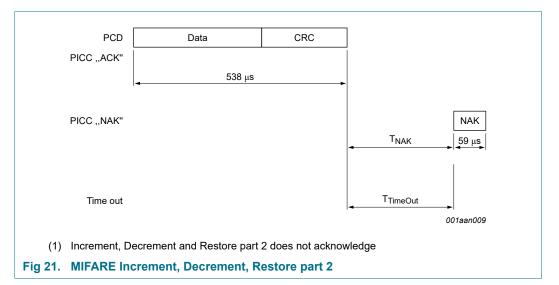
All three commands are responding with a NAK to the first command part if the addressed block is not formatted to be a valid value block, see <u>Section 8.6.2.1</u>.

The two parts of each command are shown in Figure 20 and Figure 21 and Table 26.

Table 27 shows the required timing.



#### MIFARE Classic EV1 1K - Mainstream contactless smart card IC



#### Table 26. MIFARE Increment, Decrement and Restore command

Name	Code	Description	Length
Cmd	C1h	Increment	1 byte
Cmd	C0h	Decrement	1 byte
Cmd	C2h	Restore	1 byte
Addr	-	MIFARE source block address (00h to FFh)	1 byte
CRC	-	CRC according to <u>Ref. 4</u>	2 bytes
Data	-	Operand (4 byte signed integer)	4 bytes
NAK	see <u>Table 10</u>	see <u>Section 9.3</u> 4-bit	

#### Table 27. MIFARE Increment, Decrement and Restore timing

	T <sub>ACK</sub> min	T <sub>ACK</sub> max	T <sub>NAK min</sub>	T <sub>NAK max</sub>	T <sub>TimeOut</sub>
Increment, Decrement, and Restore part 1	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	5 ms
Increment, Decrement, and Restore part 2	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	5 ms

**Remark:** The minimum required time between MIFARE Increment, Decrement, and Restore part 1 and part 2 is the minimum required FDT according to <u>Ref. 4</u>. There is no maximum time specified.

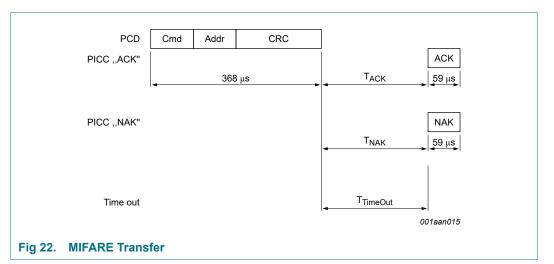
**Remark:** The MIFARE Increment, Decrement, and Restore commands require a MIFARE Transfer to store the value into a destination block.

**Remark:** The MIFARE Increment, Decrement, and Restore command part 2 does not provide an acknowledgement, so the regular time out has to be used instead.

### 12.5 MIFARE Transfer

The MIFARE Transfer requires a destination block address, and writes the value stored in the Transfer Buffer into one MIFARE Classic block. The command structure is shown in Figure 22 and Table 28.

Table 29 shows the required timing.



#### Table 28. MIFARE Transfer command

Name	Code	Description	Length
Cmd	B0h	Write the value from the Transfer Buffer into destination block	1 byte
Addr	-	MIFARE destination block address (00h to FFh)	1 byte
CRC	-	CRC according to <u>Ref. 4</u>	2 bytes
NAK	see Table 10	see <u>Section 9.3</u>	4-bit

#### Table 29. MIFARE Transfer timing

	T <sub>ACK</sub> min	T <sub>ACK</sub> max	T <sub>NAK min</sub>	T <sub>NAK max</sub>	T <sub>TimeOut</sub>
Transfer	n=9	T <sub>TimeOut</sub>	n=9	T <sub>TimeOut</sub>	10 ms

### **13. Limiting values**

Stresses above one or more of the limiting values may cause permanent damage to the device. Exposure to limiting values for extended periods may affect device reliability.

#### Table 30. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Min	Max	Unit
l <sub>l</sub>	input current	-	30	mA
P <sub>tot</sub> /pack	total power dissipation per package	-	120	mW
T <sub>stg</sub>	storage temperature	-55	125	°C
T <sub>amb</sub>	ambient temperature	-25	70	°C
V <sub>ESD</sub>	electrostatic discharge voltage on LA/LB [1]	2	-	kV

[1] ANSI/ESDA/JEDEC JS-001; Human body model: C = 100 pF, R =  $1.5 \text{ k}\Omega$ 

### **14. Characteristics**

Table 31. Characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Ci	input capacitance		<u>[1]</u>	14.9	16.9	19.0	pF
f <sub>i</sub>	input frequency			-	13.56	-	MHz
EEPROM characteristics							
t <sub>ret</sub>	retention time	T <sub>amb</sub> = 22 °C		10	-	-	year
N <sub>endu(W)</sub>	write endurance	T <sub>amb</sub> = 22 °C		100000	200000	-	cycle

[1] T<sub>amb</sub>=22°C, f=13,56Mhz, V<sub>LaLb</sub> = 1,5 V RMS

#### MIFARE Classic EV1 1K - Mainstream contactless smart card IC

## **15. Wafer specification**

For more details on the wafer delivery forms see Ref. 9.

#### Table 32. Wafer specifications MF1S50yyXDUy

Wafer         200 mm typical (8 inches)           maximum diameter after foil expansion         210 mm           thicknessMF1S50yXDUD         120 µm ± 15 µm           MF1S50yXDUF         75 µm ± 10 µm           MF1S50yXDUF         75 µm ± 10 µm           flatness         not applicable           Potential Good Dies per Wafer (PGDW)         64727           Wafer backside         and and stress relieve           material         Si           treatment         ground and stress relieve           roughness         Ra max = 0.5 µm           Rt max = 0.5 µm         Rt max = 5 µm           Rt max = 5 µm         reatment           gap between chips!!!         x = 658 µm           gap between chips!!!         typical = 19 µm           mainimum = 5 µm         mainimum = 5 µm           Passivation         sandwich structure           material         PSG / nitride           thickness         500 nm / 600 nm           Au bump (substrate connected to VSS)         sandwich structure           material         >99.9 % pure Au           hardness         35 to 80 HV 0.005           shear strength         >70 MPa           height uniformity         within a die = ±2 µm           wi	Table 52. Water specifications wit 1550yy/D0y	
maximum diameter after foil expansion210 mmthicknessMF1S50yyXDUD120 μm ± 15 μmMF1S50yyXDUF75 μm ± 10 μmflatnessnot applicablePotential Good Dies per Wafer (PGDW)64727Wafer backsidesimaterialSitreatmentground and stress relieveroughnessRa max = 0.5 μmChip dimensionssstep size[1]x = 658 μmgap between chips[1]typical = 19 μmmaterialfupical = 19 μmmaterialSitypesandwich structurematerialPSG / nitridethickness500 nm / 600 nmAu tomp (substrate connected to VSS)sto 80 HV 0.005material> 99.9 % pure Auhardness35 to 80 HV 0.005shear strengtha famheightill μmthight uniformitywithin a die = ±2 μmwithin a wafer = ±3 μmwithin a wafer = ±3 μmsizeLA, LB, VSS, TESTI2 = 66 μm × 66 μmsize variation±5 μm	Wafer	
thicknessMF1S50yyXDUD120 μm ± 15 μmMF1S50yyXDUF75 μm ± 10 μmflatnessnot applicablePotential Good Dies per Wafer (PGDW)64727Wafer backsidesimaterialSitreatmentground and stress relieveroughnessRa max = 0.5 μmRt max = 5 μmroughnessStep sizel <sup>[1]</sup> × = 658 μmy = 713 μmy = 713 μmgap between chips <sup>[1]</sup> typical = 19 μmmaterialPassivationthicknesssondwich structurematerialPSG / nitridethickness500 m/ 600 nmAu burp (substrate connected to VSS)materialhardness35 to 80 HV 0.005shear strength> 99.9 % pure Auhardness18 μmheight18 μmheight uniformitywithin a die = ±2 μmwafer to wafer = ±4 μmminimum = ±1.5 μmsize variation±5 μm	diameter	200 mm typical (8 inches)
MF1S50yyXDUF75 $\mu$ m ± 10 $\mu$ mflatnessnot applicablePotential Good Dies per Wafer (PGDW)64727Wafer backsidesimaterialSitreatmentground and stress relieveroughness $R_a max = 0.5 \mu$ mRt max = 5 $\mu$ mRt max = 5 $\mu$ mChip dimensionsx = 658 $\mu$ mstep size[1]x = 658 $\mu$ mgap between chips[1]typical = 19 $\mu$ mminium = 5 $\mu$ mminium = 5 $\mu$ mPassivationsandwich structurethickness500 nmAu bump (substrate connected to VSS)sandwich structurematerial> 99.9 % pure Auhardness35 to 80 HV 0.005shear strength> 70 MPaheight18 $\mu$ mwithin a die = ±2 $\mu$ mwithin a wafer = ±3 $\mu$ msizeLA, LB, VSS, TESTE1 = 66 $\mu$ m × 66 $\mu$ msize variation±5 $\mu$ m	maximum diameter after foil expansion	210 mm
fatness         not applicable           Potential Good Dies per Wafer (PGDW)         64727           Wafer backside         si           material         Si           treatment         ground and stress relieve           roughness         R <sub>a</sub> max = 0.5 µm           roughness         R <sub>a</sub> max = 5 µm           Chip dimensions         x = 658 µm           step size[1]         X = 658 µm           gap between chips[1]         typical = 19 µm           minimum = 5 µm         minimum = 5 µm           Passivation         sandwich structure           type         sandwich structure           material         PSG / nitride           thickness         500 nm / 600 nm           Au bump (substrate connected to VSS)         site a 35 to 80 HV 0.005           shear strength         > 70 MPa           height uniformity         within a die = ±2 µm           within a wafer = ±3 µm         within a wafer = ±3 µm           size         minimum = ±1.5 µm           size variation         ±5 µm	thicknessMF1S50yyXDUD	120 μm $\pm$ 15 μm
Potential Good Dies per Wafer (PGDW) $64727$ Wafer backsidesimaterialSitreatmentground and stress relieveroughness $R_a max = 0.5 \ \mu m$ roughness $R_a max = 0.5 \ \mu m$ chip dimensions $R_i max = 5 \ \mu m$ step size[1] $x = 658 \ \mu m$ gap between chips[1]typical = 19 \ \mu mgap between chips[1]typical = 19 \ \mu mPassivationsandwich structuretypesandwich structurematerialPSG / nitridethickness500 nm / 600 nmAu bump (substrate connected to VSS)sto 80 HV 0.005material> 99.9 % pure Auhardness35 to 80 HV 0.005shear strength> 70 MPaheight18 \ \mu mheight uniformitywithin a die = $\pm 2 \ \mu m$ flatnessminimum = $\pm 1.5 \ \mu m$ sizeLA, LB, VSS, TESTI2 = 66 \ \mu m × 66 \ \mu m	MF1S50yyXDUF	75 $\mu$ m $\pm$ 10 $\mu$ m
Wafer backsideSimaterialSitreatmentground and stress relieveroughness $R_a max = 0.5 \ \mu m$ roughness $R_t max = 5 \ \mu m$ Chip dimensionsstep size[1]step size[1] $x = 658 \ \mu m$ gap between chips[1] $y = 713 \ \mu m$ gap between chips[1]typical = 19 \ \mu mminimum = 5 \ \mu mPassivationsandwich structuretypesandwich structurematerialPSG / nitridethickness500 nm / 600 nmAu bump (substrate connected to VSS)sto 80 HV 0.005shear strength> 70 MPaheight18 \ \m mheight18 \ \m mfatnessminimum = ±1.2 \ \m msizeLA, LB, VSS, TEST[2] = 66 \ \m m < 66 \ \m m	flatness	not applicable
materialSimaterialground and stress relieveroughness $R_a max = 0.5 \ \mu m$ $R_t max = 0.5 \ \mu m$ $R_t max = 5 \ \mu m$ Chip dimensionsstep sizel <sup>11</sup> x = 658 \ \mu my = 713 \ \mu mgap between chips <sup>[11]</sup> y = 713 \ \mu mminimum = 5 \ \mu mPassivationtypesandwich structurematerialPSG / nitridethickness500 nm / 600 nmAu bump (substrate connected to VSS)material> 99.9 % pure Auhardness35 to 80 HV 0.005shear strength> 70 MPaheight18 \ \mu mheight uniformitywithin a die = $\pm 2 \ \mu m$ materialsafer = $\pm 3 \ \mu m$ wafer to wafer = $\pm 4 \ \mu m$ flatnessminimum = $\pm 1.5 \ \mu m$ sizeLA, LB, VSS, TEST <sup>[2]</sup> = 66 \ \mu m < 66 \ \mu msize variation	Potential Good Dies per Wafer (PGDW)	64727
treatmentground and stress relieveroughness $R_a max = 0.5 \ \mu m$ $R_t max = 5 \ \mu m$ $R_t max = 5 \ \mu m$ Chip dimensions $x = 658 \ \mu m$ step size[1] $x = 658 \ \mu m$ $gap$ between chips[1] $typical = 19 \ \mu m$ minimum = 5 \ $\mu m$ Passivationtypical = 19 \ \mu m minimum = 5 \ $\mu m$ Passivation $typical = 19 \ \mu m$ minimum = 5 \ $\mu m$ Au bump (substrate connected to VSS) $S00 \ nm / 600 \ nm$ Au bump (substrate connected to VSS) $son W 0.005$ material> 99.9 \% \ pure Au hardnesshardness $35 \ to 80 \ HV 0.005$ shear strength> 70 \ MPaheight $18 \ \mu m$ wafer to wafer = $\pm 3 \ \mu m$ wafer to wafer = $\pm 3 \ \mu m$ flatnessminimum = $\pm 1.5 \ \mu m$ sizeLA, LB, VSS, TEST[2] = 66 \ \mu m \times 66 \ \mu m size variation	Wafer backside	
roughness $R_a max = 0.5 \ \mu m$ $R_t max = 5 \ \mu m$ Chip dimensionsx = 658 \ \mu m y = 713 \ \mu mstep size[1]x = 658 \ \mu m y = 713 \ \mu mgap between chips[1]typical = 19 \ \mu m minimum = 5 \ \mu mPassivationtypical = 19 \ \mu m minimum = 5 \ \mu mPassivationsandwich structurematerialPSG / nitridethickness500 nm / 600 nmAu bump (substrate connected to VSS)verticalmaterial> 99.9 % pure Au hardnessheight18 \ \mu m within a die = $\pm 2 \ \mu m$ within a wafer = $\pm 3 \ \mu m$ height uniformitywithin a wafer = $\pm 3 \ \mu m$ wafer to wafer = $\pm 4 \ \mu m$ flatnessminimum = $\pm 1.5 \ \mu m$ sizeLA, LB, VSS, TEST[2] = 66 \ \mu m × 66 \ \mu m size variation	material	Si
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thickness500 nm / 600 nmAu bump (substrate connected to VSS) $> 99.9 \%$ pure Aumaterial> 99.9 % pure Auhardness35 to 80 HV 0.005shear strength> 70 MPaheight18 µmheight uniformitywithin a die = ±2 µmwithin a wafer = ±3 µmwafer to wafer = ±4 µmflatnessminimum = ±1.5 µmsizeLA, LB, VSS, TEST[2] = 66 µm × 66 µmsize variation±5 µm	type	sandwich structure
Au bump (substrate connected to VSS) $> 99.9 \%$ pure Aumaterial> 99.9 % pure Auhardness $35 \text{ to } 80 \text{ HV } 0.005$ shear strength> 70 MPaheight $18 \mu \text{m}$ height uniformitywithin a die = $\pm 2 \mu \text{m}$ within a wafer = $\pm 3 \mu \text{m}$ mater to wafer = $\pm 4 \mu \text{m}$ flatnessminimum = $\pm 1.5 \mu \text{m}$ sizeLA, LB, VSS, TEST[2] = 66 \mu m × 66 \mu msize variation $\pm 5 \mu \text{m}$	material	PSG / nitride
material> 99.9 % pure Auhardness35 to 80 HV 0.005shear strength> 70 MPaheight18 $\mu$ mheight uniformitywithin a die = $\pm 2 \mu$ mminimum = $\pm 3 \mu$ mwithin a wafer = $\pm 3 \mu$ mflatnessminimum = $\pm 1.5 \mu$ msizeLA, LB, VSS, TEST[2] = 66 $\mu$ m × 66 $\mu$ msize variation $\pm 5 \mu$ m	thickness	500 nm / 600 nm
hardness $35 \text{ to } 80 \text{ HV } 0.005$ shear strength> 70 MPaheight $18 \ \mu\text{m}$ height uniformitywithin a die = $\pm 2 \ \mu\text{m}$ within a wafer = $\pm 3 \ \mu\text{m}$ within a wafer = $\pm 3 \ \mu\text{m}$ flatnessminimum = $\pm 1.5 \ \mu\text{m}$ sizeLA, LB, VSS, TEST[2] = $66 \ \mu\text{m} \times 66 \ \mu\text{m}$ size variation $\pm 5 \ \mu\text{m}$	Au bump (substrate connected to VSS)	
shear strength> 70 MPaheight18 $\mu$ mheight uniformitywithin a die = $\pm 2 \mu$ m $\mu$ within a wafer = $\pm 3 \mu$ mflatnessminimum = $\pm 1.5 \mu$ msizeLA, LB, VSS, TEST[2] = 66 $\mu$ m × 66 $\mu$ msize variation $\pm 5 \mu$ m	material	> 99.9 % pure Au
$      height \\ height uniformity \\ height uniformity \\                                   $	hardness	35 to 80 HV 0.005
height uniformitywithin a die = $\pm 2 \mu m$ within a wafer = $\pm 3 \mu m$ wafer to wafer = $\pm 4 \mu m$ flatnessminimum = $\pm 1.5 \mu m$ sizeLA, LB, VSS, TEST[2] = $66 \mu m \times 66 \mu m$ size variation $\pm 5 \mu m$	shear strength	> 70 MPa
within a wafer = $\pm 3 \ \mu m$ within a wafer = $\pm 3 \ \mu m$ wafer to wafer = $\pm 4 \ \mu m$ flatnessminimum = $\pm 1.5 \ \mu m$ sizeLA, LB, VSS, TEST[2] = $66 \ \mu m \times 66 \ \mu m$ size variation $\pm 5 \ \mu m$	height	18 μm
wafer to wafer = $\pm 4 \ \mu m$ flatnessminimum = $\pm 1.5 \ \mu m$ sizeLA, LB, VSS, TEST <sup>[2]</sup> = $66 \ \mu m \times 66 \ \mu m$ size variation $\pm 5 \ \mu m$	height uniformity	within a die = $\pm 2 \ \mu m$
flatnessminimum = $\pm 1.5 \ \mu m$ sizeLA, LB, VSS, TEST[2] = $66 \ \mu m \times 66 \ \mu m$ size variation $\pm 5 \ \mu m$		within a wafer = $\pm 3 \ \mu m$
sizeLA, LB, VSS, TEST <sup>[2]</sup> = 66 μm × 66 μmsize variation±5 μm		wafer to wafer = $\pm 4 \ \mu m$
size variation ±5 μm	flatness	minimum = $\pm 1.5 \ \mu m$
	size	LA, LB, VSS, TEST[2] = 66 μm × 66 μm
under bump metallization sputtered TiW	size variation	±5 μm
	under bump metallization	sputtered TiW

[1] The step size and the gap between chips may vary due to changing foil expansion

[2] Pads VSS and TESTIO are disconnected when wafer is sawn.

### 15.1 Fail die identification

Electronic wafer mapping covers the electrical test results and additionally the results of mechanical/visual inspection. No ink dots are applied.

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#### 15.2 Package outline

For more details on the contactless modules MOA4 and MOA8 please refer to  $\frac{\text{Ref. 7}}{\text{Ref. 8}}$  and Ref. 8.

PLLMC: plastic leadless module carrier package; 35 mm wide tape

SOT500-2

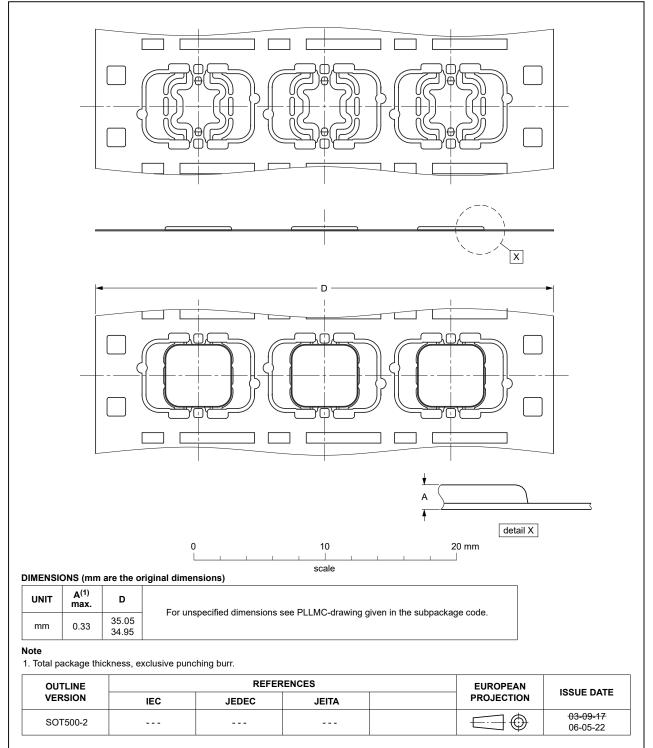


Fig 23. Package outline SOT500-2

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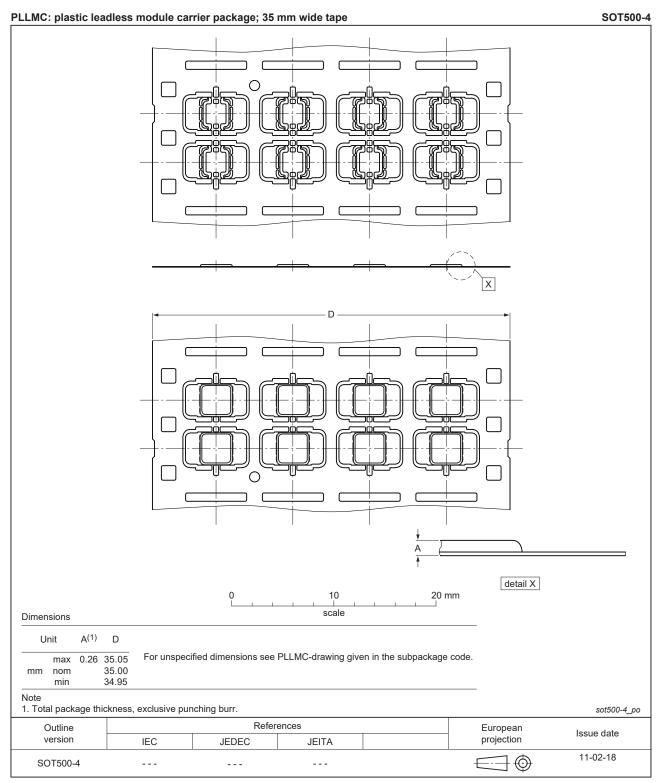


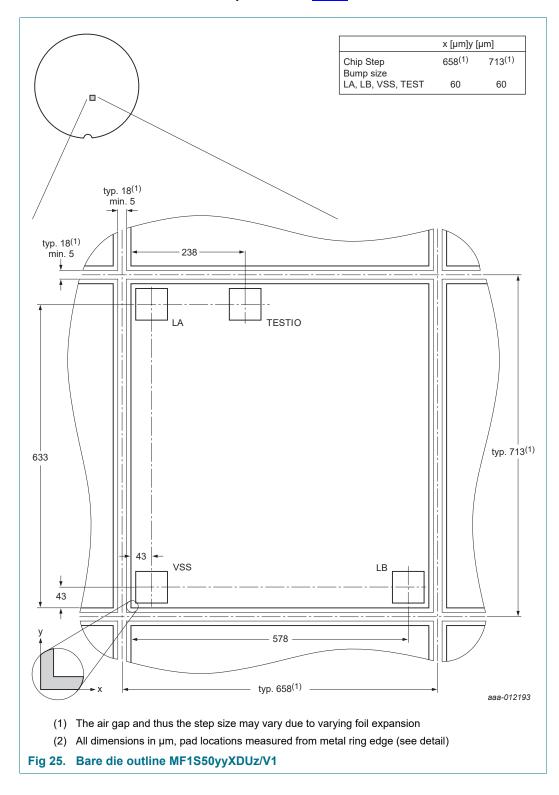
Fig 24. Package outline SOT500-4

MF1S50yyX\_V1

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## 16. Bare die outline

For more details on the wafer delivery forms, see Ref. 9.



MF1S50yyX_V1	
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### **17. Abbreviations**

Table 33. Abbre	viations and symbols
Acronym	Description
ACK	ACKnowledge
ATQA	Answer To reQuest, Type A
CRC	Cyclic Redundancy Check
СТ	Cascade Tag (value 88h) as defined in ISO/IEC 14443-3 Type A
EEPROM	Electrically Erasable Programmable Read-Only Memory
FDT	Frame Delay Time
FFC	Film Frame Carrier
IC	Integrated Circuit
LCR	L = inductance, Capacitance, Resistance (LCR meter)
LSB	Least Significant Bit
NAK	Not AcKnowledge
NUID	Non-Unique IDentifier
NV	Non-Volatile memory
PCD	Proximity Coupling Device (Contactless Reader)
PICC	Proximity Integrated Circuit Card (Contactless Card)
REQA	REQuest command, Type A
RID	Random ID
RF	Radio Frequency
RMS	Root Mean Square
RNG	Random Number Generator
SAK	Select AcKnowledge, type A
SECS-II	SEMI Equipment Communications Standard part 2
TiW	Titanium Tungsten
UID	Unique IDentifier
WUPA	Wake-Up Protocol type A

### **18. References**

- [1] MIFARE (Card) Coil Design Guide Application note, BU-ID Document number 0117\*\*1
- [2] MIFARE Type Identification Procedure Application note, BU-ID Document number 0184\*\*1
- [3] ISO/IEC 14443-2 2001
- [4] ISO/IEC 14443-3 2001
- [5] MIFARE & I-CODE CL RC632 Multiple protocol contactless reader IC Product data sheet

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<sup>1. \*\* ...</sup> document version number

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- [6] MIFARE and handling of UIDs Application note, BU-ID Document number 1907\*\*1
- [7] Contactless smart card module specification MOA4 Delivery Type Description, BU-ID Document number 0823\*\*1
- [8] Contactless smart card module specification MOA8 Delivery Type Description, BU-ID Document number 1636\*\*1
- [9] General specification for 8" wafer on UV-tape; delivery types Delivery Type Description, BU-ID Document number 1005\*\*1

MIFARE Classic EV1 1K - Mainstream contactless smart card IC

## **19. Revision history**

Table 34. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
MF1S50yyX/V1 v.3.0	20140303	Product data sheet	-	-

MIFARE Classic EV1 1K - Mainstream contactless smart card IC

### 20. Legal information

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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MIFARE Classic EV1 1K - Mainstream contactless smart card IC

## 22. Tables

Table 1.	Quick reference data	n
Table 1.	Ordering information	
Table 3.	Pin allocation table	
Table 3.	Value block format example	
Table 5.	Memory operations.	
Table 5.		
	Access conditions	
Table 7.	Access conditions for the sector trailer	
Table 8.		
Table 9.		
Table 10.	MIFARE ACK and NAK	
Table 11.	ATQA response of the MF1S50yyX/V1	
Table 12.	SAK response of the MF1S50yyX/V1	
Table 13.	Personalize UID Usage command	
Table 14.	Personalize UID Usage timing	.19
Table 15.	Available activation sequences for 7-byte UID	
	options	.20
Table 16.	Input parameter to MIFARE Classic	
	Authenticate	
Table 17.		
Table 18.		
Table 19.	Load Modulation Status Indication	
Table 20.	MIFARE authentication command	.22
Table 21.	MIFARE authentication timing	
Table 22.	MIFARE Read command	
Table 23.	MIFARE Read timing	
Table 24.	MIFARE Write command	.24
Table 25.	MIFARE Write timing	.25
Table 26.	MIFARE Increment, Decrement and Restore	
	command	.26
Table 27.	MIFARE Increment, Decrement and Restore	
	timing	.26
Table 28.	MIFARE Transfer command	.27
Table 29.	MIFARE Transfer timing	.27
Table 30.	Limiting values	.28
Table 31.	Characteristics	
Table 32.	Wafer specifications MF1S50yyXDUy	
Table 33.	Abbreviations and symbols	
Table 34.	Revision history	
	•	

MIFARE Classic EV1 1K - Mainstream contactless smart card IC

## 23. Figures

Fig 1.	Contactless MIFARE system
Fig 2.	Block diagram of MF1S50yyX/V1
Fig 3.	Pin configuration for SOT500-2 (MOA4)4
Fig 4.	MIFARE Classic command flow diagram 6
Fig 5.	Memory organization
Fig 6.	Manufacturer block for MF1S503yX with 4-byte
	NUID
Fig 7.	Manufacturer block for MF1S500yX with 7-byte
	UID
Fig 8.	Value blocks10
Fig 9.	Sector trailer
Fig 10.	Access conditions
Fig 11.	Frame Delay Time (from PCD to PICC)
	and $T_{ACK}$ and $T_{NAK}$
Fig 12.	Personalize UID Usage
Fig 13.	SET_MOD_TYPE21
Fig 14.	Byte Location of Load Modulation Status in
	Block 0 / Sector 0
Fig 15.	MIFARE Authentication part 1
Fig 16.	MIFARE Authentication part 2
Fig 17.	MIFARE Read23
Fig 18.	MIFARE Write part 1
Fig 19.	MIFARE Write part 2
Fig 20.	MIFARE Increment, Decrement, Restore part 1 . 25
Fig 21.	MIFARE Increment, Decrement, Restore part 2 . 26
Fig 22.	MIFARE Transfer
Fig 23.	Package outline SOT500-2
Fig 24.	Package outline SOT500-4
Fig 25.	Bare die outline MF1S50yyXDUz/V1
32	

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## MF1S50yyX/V1

MIFARE Classic EV1 1K - Mainstream contactless smart card IC

### 24. Contents

1	General description 1
1.1	Anticollision
1.2	Simple integration and user convenience 1
1.3	Security and privacy
1.4	Delivery options 2
2	Features and benefits 2
2.1	EEPROM 2
3	Applications 2
4	Quick reference data 2
5	Ordering information 3
6	Block diagram 3
7	Pinning information 4
7.1	Pinning 4
8	Functional description 5
8.1	Block description
8.2	Communication principle
8.2.1	Request standard / all
8.2.2	Anticollision loop
8.2.3	Select card
8.2.4	Three pass authentication
8.2.5	Memory operations
8.3	Data integrity
8.4	Three pass authentication sequence
8.5	RF interface 8
8.6	Memory organization
8.6.1	Manufacturer block
8.6.2	Data blocks9
8.6.2.1	Value blocks
8.6.3	Sector trailer 1 0
8.7	Memory access
8.7.1	Access conditions
8.7.2	Access conditions for the sector trailer 1 3
8.7.3	Access conditions for data blocks 14
9	Command overview 15
9.1	MIFARE Classic command overview 1 5
9.2	Timings
9.3	MIFARE Classic ACK and NAK 1 7
9.4	ATQA and SAK responses
10	UID Options and Handling 18
10.1	7-byte UID Operation
10.1.1	Personalization Options
10.1.2	Anti-collision and Selection
10.1.2	Authentication
10.1.0	4-byte UID Operation
10.2.1	Anti-collision and Selection
10.2.1	Authentication
	Σ

11	Load Modulation Strength Option	20
12	MIFARE Classic commands	22
12.1	MIFARE Authentication	22
12.2	MIFARE Read	23
12.3	MIFARE Write	24
12.4	MIFARE Increment, Decrement and Restore	25
12.5	MIFARE Transfer	27
13	Limiting values	28
14	Characteristics	28
15	Wafer specification	29
15.1	Fail die identification	29
15.2	Package outline	30
16	Bare die outline	32
17	Abbreviations	33
18	References	33
19	Revision history	35
20	Legal information	36
20.1	Data sheet status	36
20.2	Definitions	36
20.3	Disclaimers	36
20.4	Trademarks	37
21	Contact information	37
22	Tables	38
23	Figures	39
24	Contents	40

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